GOOD-ARK SEMICONDUCTOR

GSBAS70LP

Schottky Diode

Features

- Low current rectification
- Low forward voltage

DFN1006

Mechanical Data

- Case: DFN1006
- Terminals: solderable per MIL-STD-202, Method 208

Schematic Diagram

Absolute Maximum Ratings (T_A=25°C unless otherwise specified)

Parameter	Symbol	Value	Unit
Power Dissipation	P_D	200	mW
Reverse Voltage	V_R	70	V
Average Forward Current	$I_{F(AV)}$	70	mA
Non-Repetitive Peak Forward Current (t=1s)	I_{FSM}	100	mA
Junction Temperature	T_J	150	°C
Storage Temperature	T_{STG}	-65 to +150	°C

Electrical Characteristics (T_A=25°C unless otherwise specified)

Parameter	Symbol	Conditions	Min	Typ	Max	Unit
Reverse Leakage Current	I_R	V_R=50V	-	0.01	0.2	uA
Forward Voltage	V_F	I_F=1mA	-	-	0.41	V
		I_F=15mA	-	-	1	V
Reverse Voltage	V_R	I_R=10uA	70	-	-	V
Typical Junction Capacitance	C_J	V_R=0V, F=1.0MHz	-	-	2	pF
Reverse Recovery Time	T_{RR}	I_F=I_R=10mA, I_{RR}=1mA, R_L=100Ω	-	-	5	ns

Typical Characteristic Curves

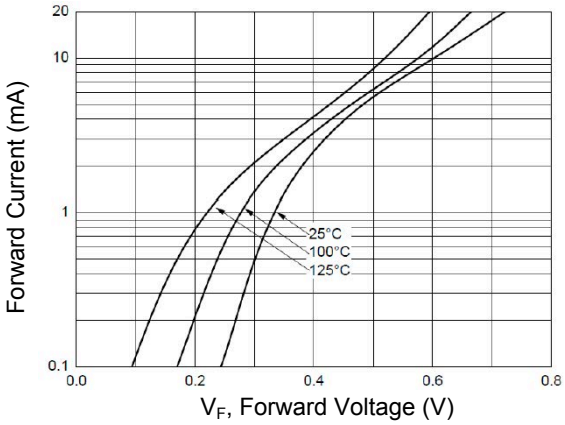


Figure 1. Forward Characteristics

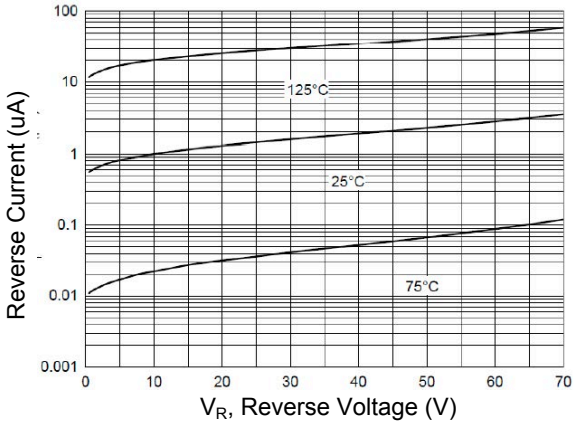


Figure 2. Reverse Characteristics

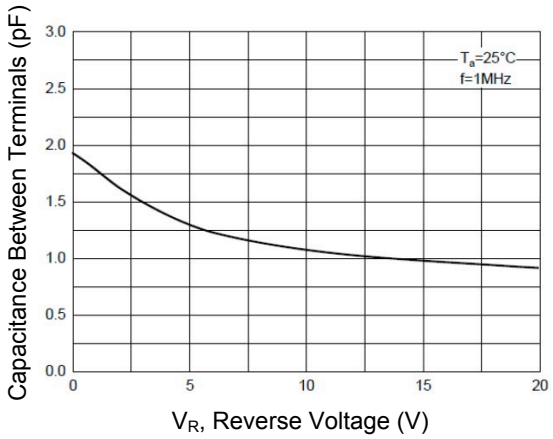


Figure 3. Capacitance Characteristics

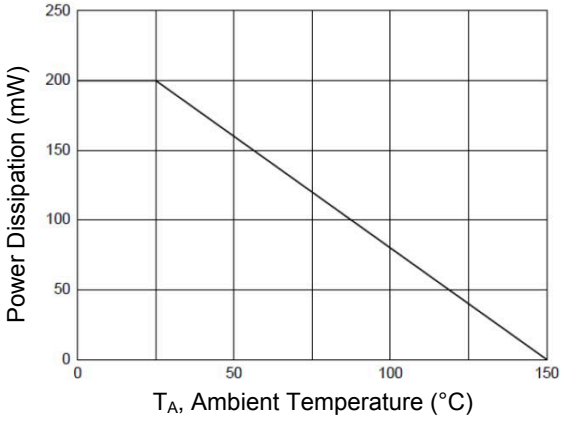


Figure 4. Power Derating Curve

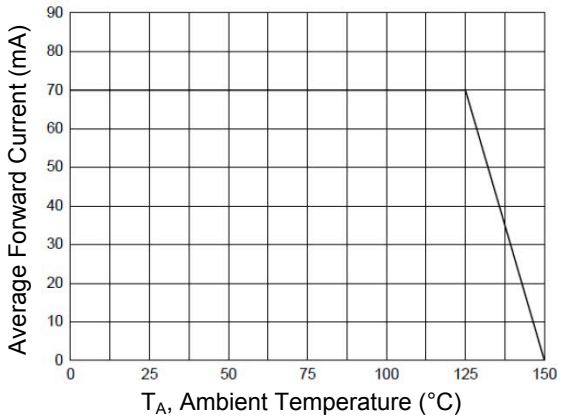
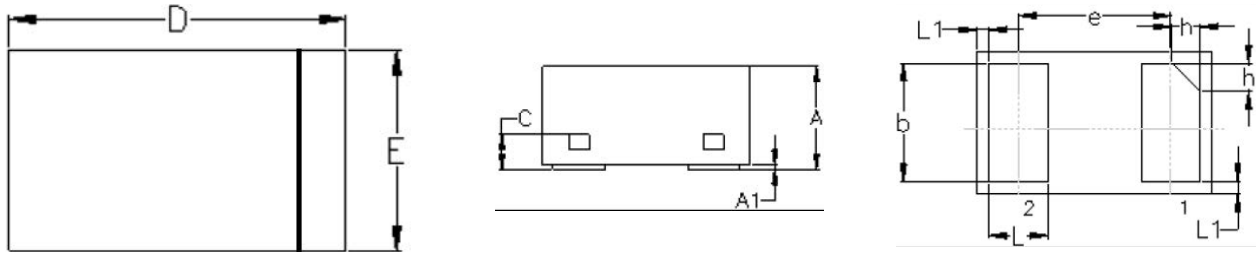


Figure 5. Current Derating Curve

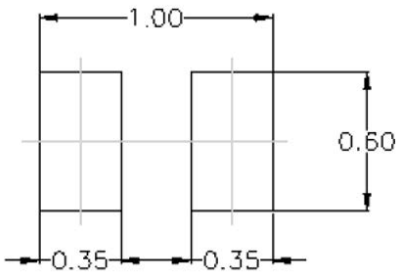
Package Outline Dimension (DFN1006)



Cathode Band

Symbol	Dimensions in Millimeters		
	Min	Nom	Max
A	0.45	0.50	0.55
A1	0.00	0.02	0.05
b	0.45	0.50	0.55
C	0.12	0.15	0.18
D	0.95	1.00	1.05
e	0.65 BSC		
E	0.55	0.60	0.65
L	0.20	0.25	0.30
L1	0.05 REF.		
h	0.07	0.12	0.17

Recommended Pad Layout



(Unit:mm)

Order Information

Device	Package	Marking	Carrier	Quantity
GSBAS70LP	DFN1006	S5.	Tape & Reel	10,000 pcs / Reel